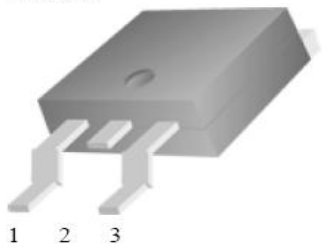
General Description：

CS4N80 A4HD, the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-252, which accords with the RoHS standard.

V_{DSS}	800	V
I_D	4	A
$P_D(T_C=25℃)$	100	W
$R_{DS(ON)Typ}$	2.2	Ω

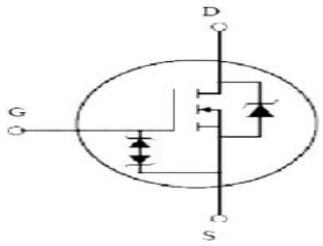
TO-252



1 2 3

1.Gate 2.Drain 3.Source

Inner Equivalent Principium Chart



Features：

- **Fast Switching**
- **ESD Improved Capability**
- **Low Gate Charge (Typical Data: 25nC)**
- **Low Reverse transfer capacitances(Typical:7.5pF)**
- **100% Single Pulse avalanche energy Test**

Applications：

Power switch circuit of adaptor and charger.

Absolute（Tc= 25℃ unless otherwise specified）：

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	800	V
I_D	Continuous Drain Current	4	A
	Continuous Drain Current T_C = 100 °C	2.5	A
I_{DM} [a1]	Pulsed Drain Current	16	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS} [a2]	Single Pulse Avalanche Energy	230	mJ
dv/dt [a3]	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	100	W
	Derating Factor above 25°C	0.8	W/℃
$V_{ESD(G-S)}$	Gate source ESD (HBM-C= 100pF, R=1.5kΩ)	4000	V
T_J，T_{stg}	Operating Junction and Storage Temperature Range	150，–55 to 150	℃
T_L	Maximum Temperature for Soldering	300	℃

Electrical Characteristics（Tc= 25℃ unless otherwise specified）：

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Unit
			Min.	Typ.	Max.	s
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	800	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	ID=250uA,Reference25℃	--	0.9	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS} =800V, V_{GS}= 0V, T_a = 25℃	--	--	25	μA
		V_{DS} =640V, V_{GS}= 0V, T_a = 125℃	--	--	250	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+20V	--	--	10	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-20V	--	--	-10	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=2A	--	2.2	2.8	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	--	4.0	V
Pulse width tp≤300μs, δ ≤2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Trans conductance	V_{DS}=15V, I_D =2A	--	5.5	--	S
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1.0MHz	--	865	--	pF
C_{oss}	Output Capacitance		--	82	--	
C_{rss}	Reverse Transfer Capacitance		--	7.5	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =4A V_{DD} = 400V R_G =10Ω	--	18	--	ns
tr	Rise Time		--	16	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	45	--	
t_f	Fall Time		--	14	--	
Q_g	Total Gate Charge	I_D =4A V_{DD} =640V V_{GS} = 10V	--	25	--	nC
Q_{gs}	Gate to Source Charge		--	4	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	11.5	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	4	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	16	A
V_{SD}	Diode Forward Voltage	I_S=4.0A,V_{GS}=0V	--	--	1.5	V
trr	Reverse Recovery Time	I_S=4.0A,T_j = 25℃ dI$_F$/dt=100A/us, V_{GS}=0V	--	274	--	ns
Qrr	Reverse Recovery Charge		--	1150	--	nC
I_{RRM}	Reverse Recovery Current		--	8.4	--	A
Pulse width tp≤300μs, δ ≤2%						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	1.25	℃/W
$R_{\theta JA}$	Junction-to-Ambient	100	℃/W

[a1]: Repetitive rating; pulse width limited by maximum junction temperature
[a2]: L=10mH, I_D=6.8A, Start T_J=25℃
[a3]: I_{SD} =4A,di/dt ≤100A/us,V_{DD}≤BV_{DS}, Start T_J=25℃

Characteristics Curve:

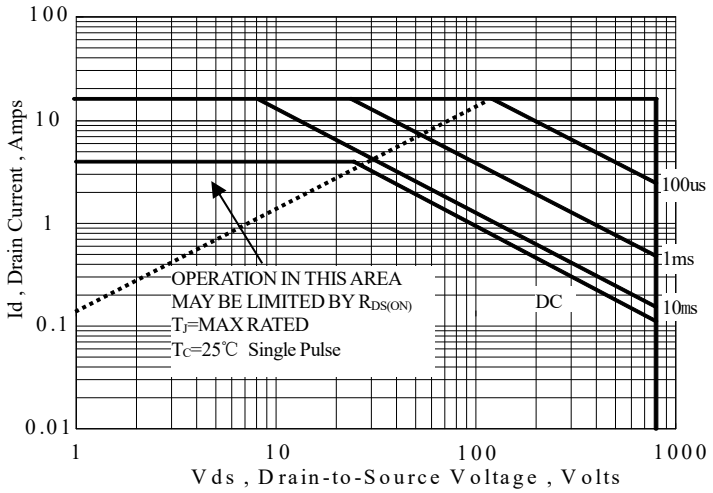


Figure 1 Maximum Forward Bias Safe Operating Area

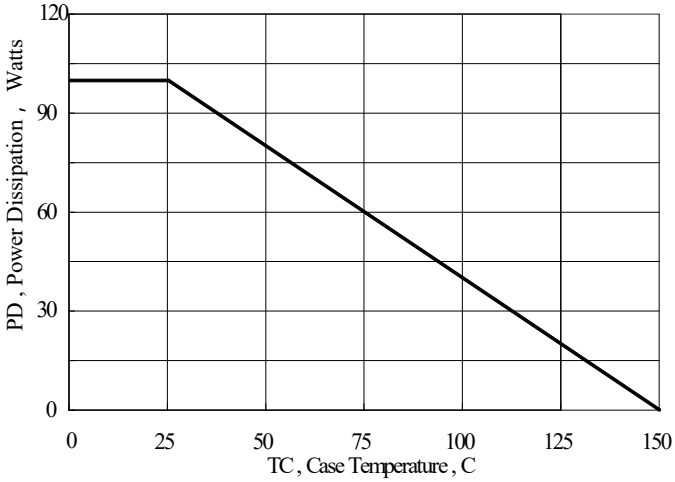


Figure 2 Maximum Power Dissipation vs Case Temperature

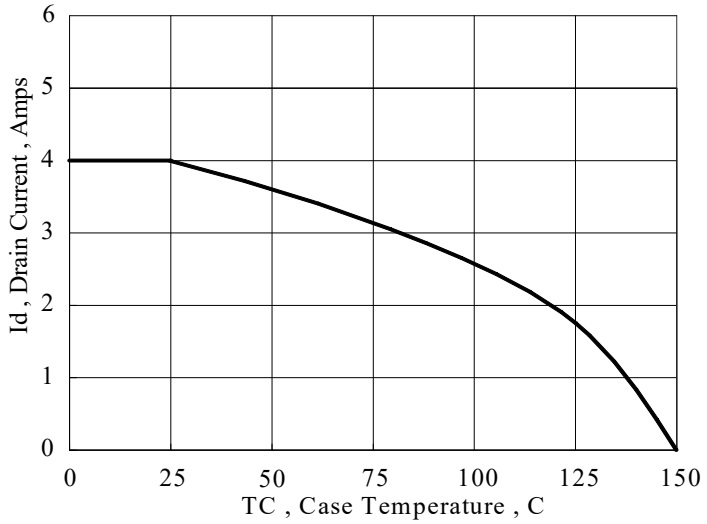


Figure 3 Maximum Continuous Drain Current vs Case Temperature

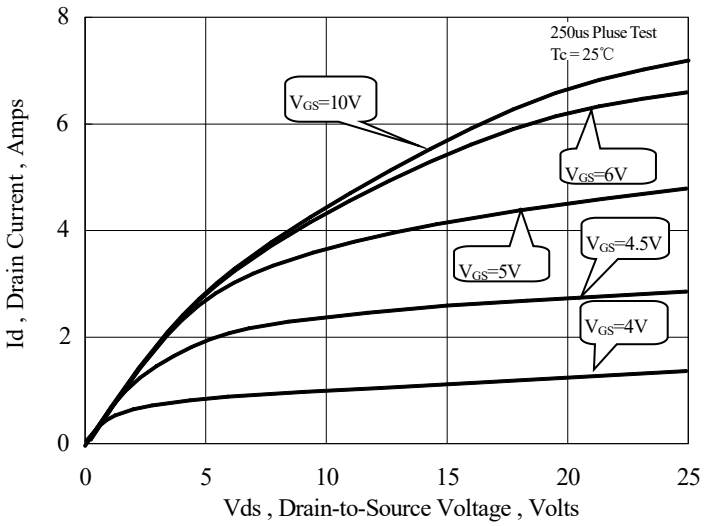


Figure 4 Typical Output Characteristics

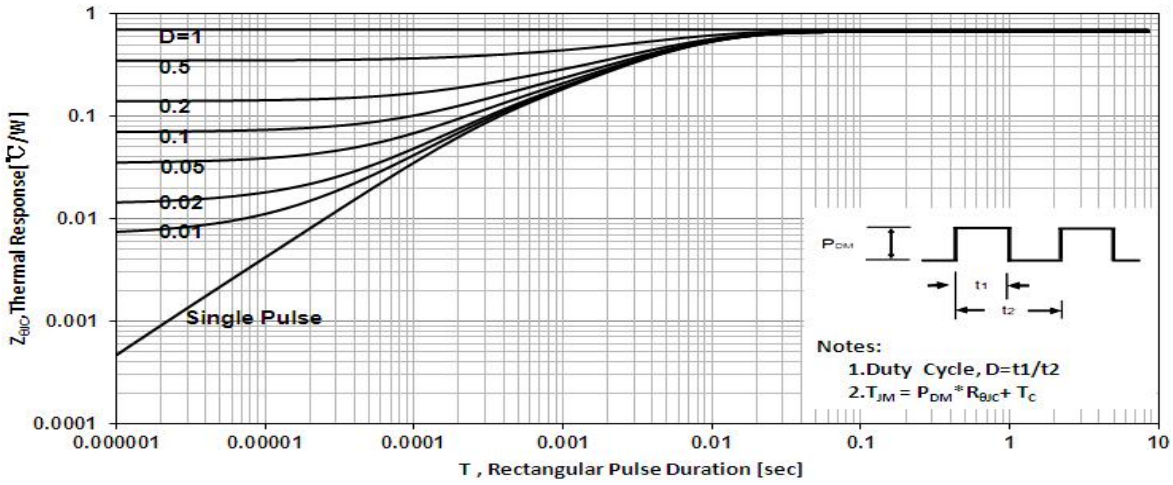


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

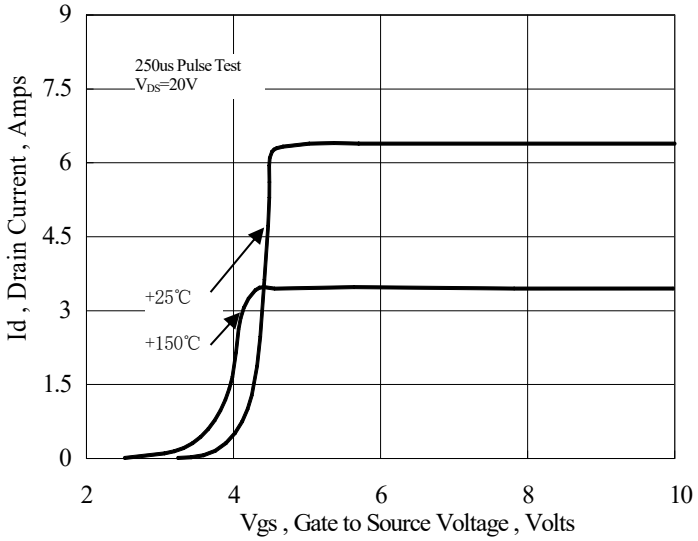


Figure 6 Typical Transfer Characteristics

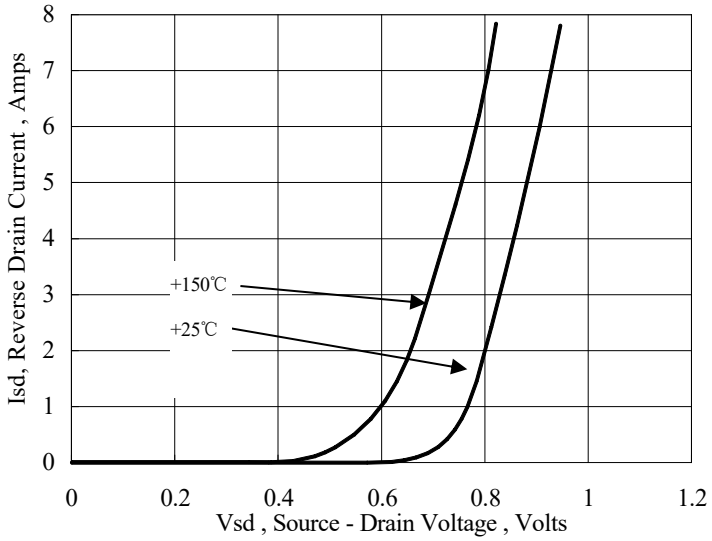


Figure 7 Typical Body Diode Transfer Characteristics

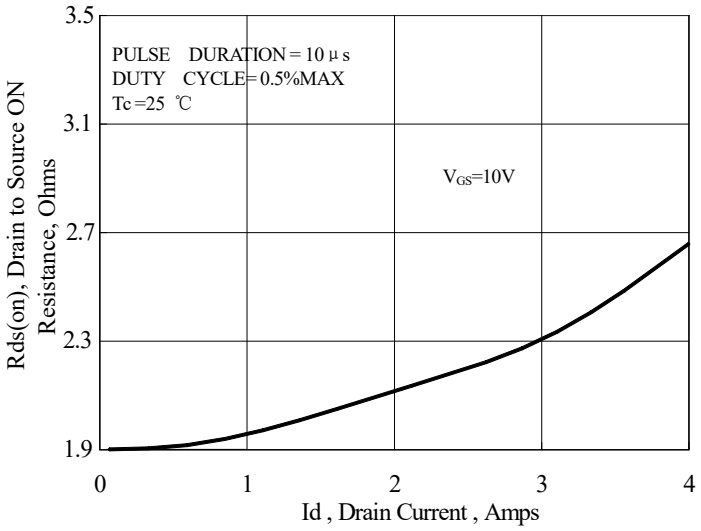


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

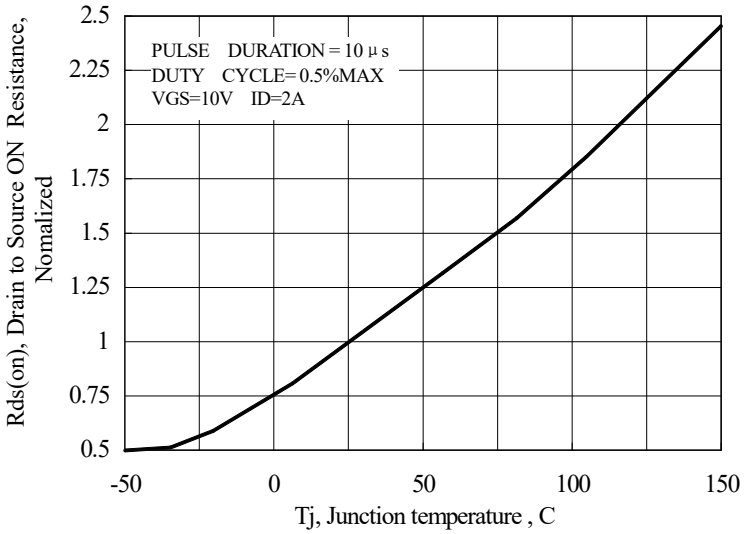


Figure 9 Typical Drian to Source on Resistance vs Junction Temperature

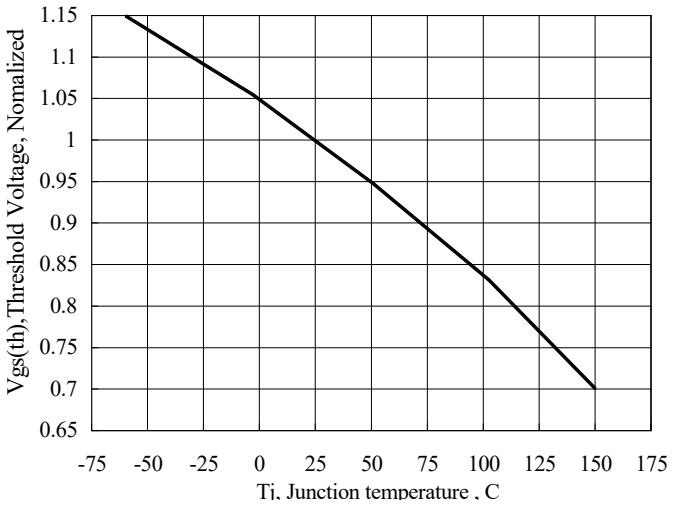


Figure 10 Typical Theshold Voltage vs Junction Temperature

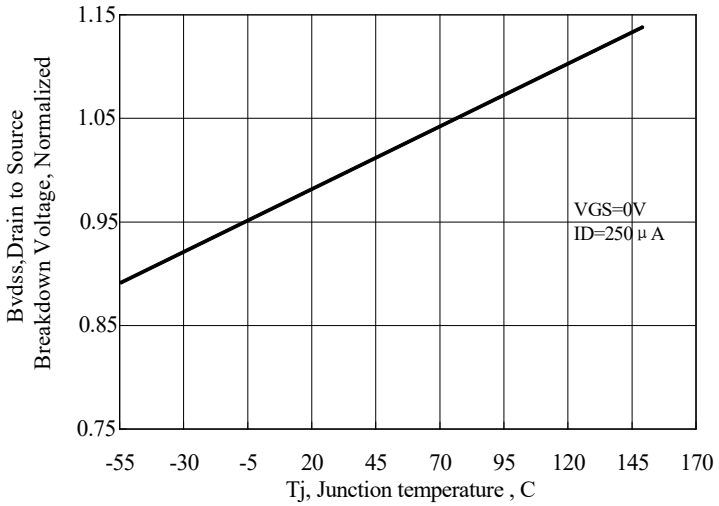


Figure 11 Typical Breakdown Voltage vs Junction Temperature

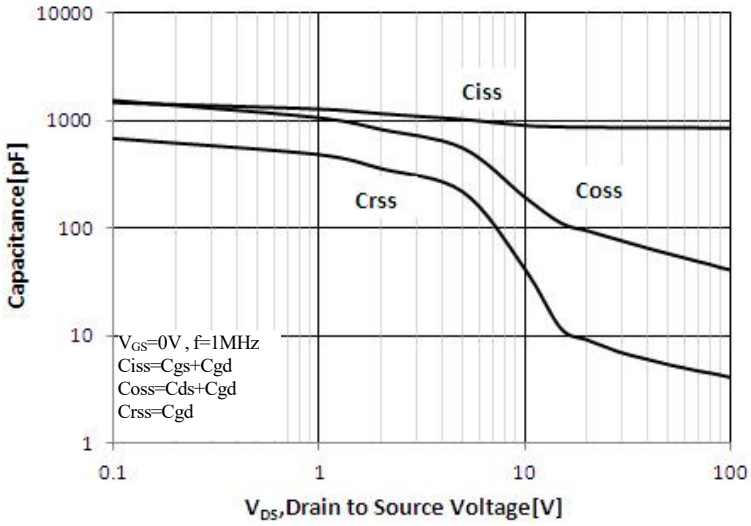


Figure 12 Typical Capacitance vs Drain to Source Voltage

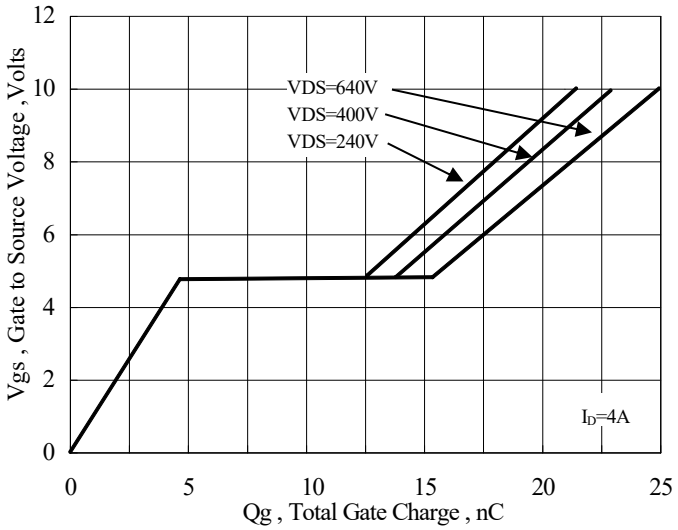


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform:

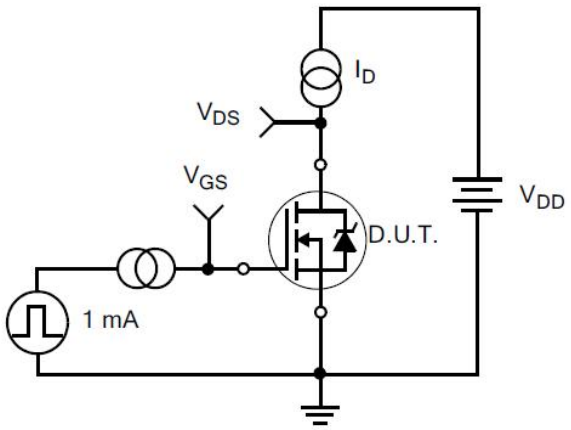


Figure 17. Gate Charge Test Circuit

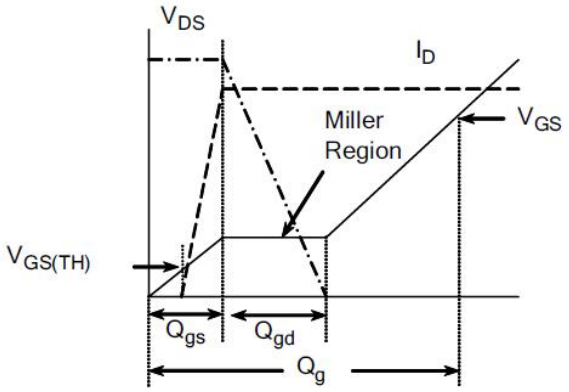


Figure 18. Gate Charge Waveform

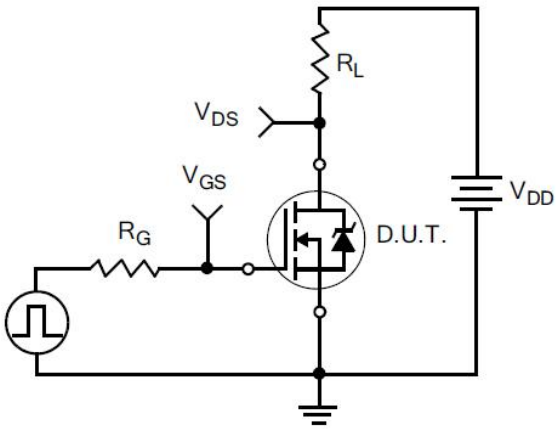


Figure 19. Resistive Switching Test Circuit

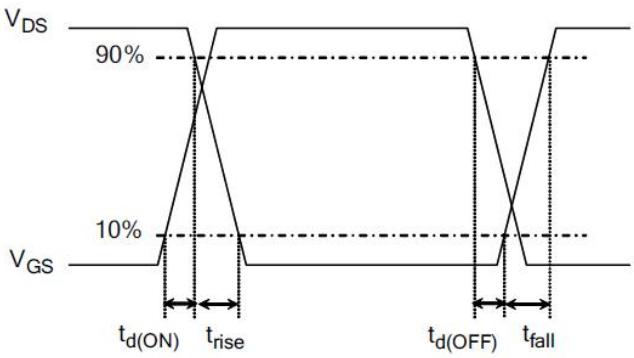


Figure 20. Resistive Switching Waveforms

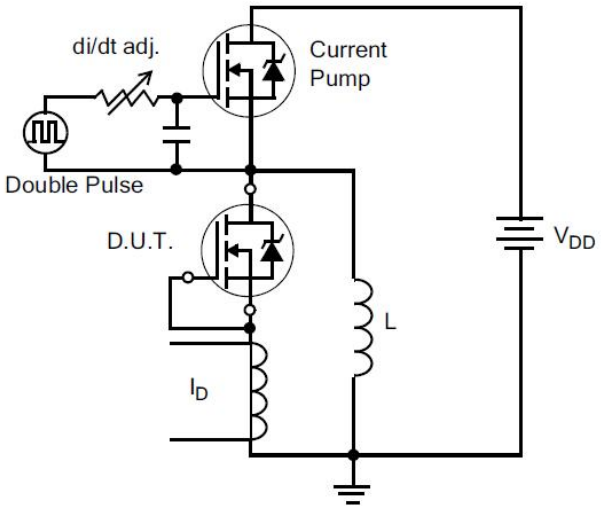


Figure 21. Diode Reverse Recovery Test Circuit

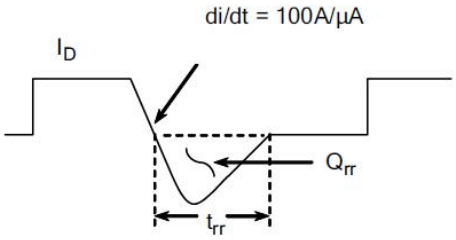


Figure 22. Diode Reverse Recovery Waveform

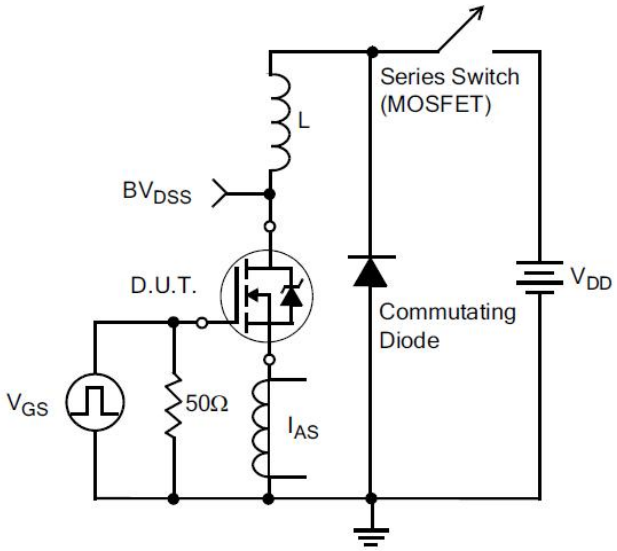
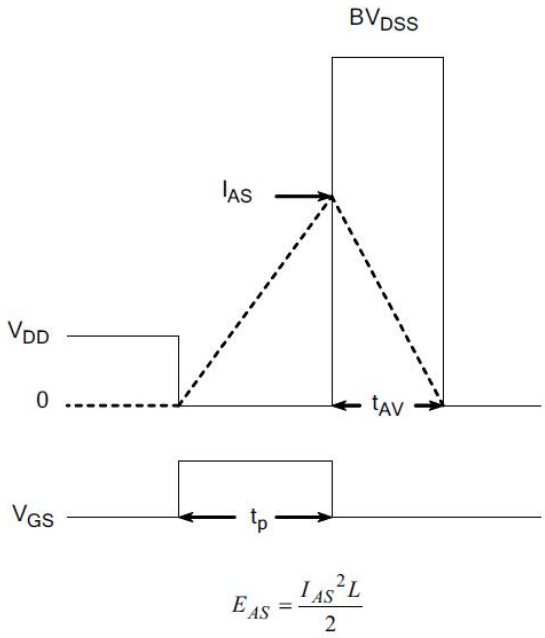


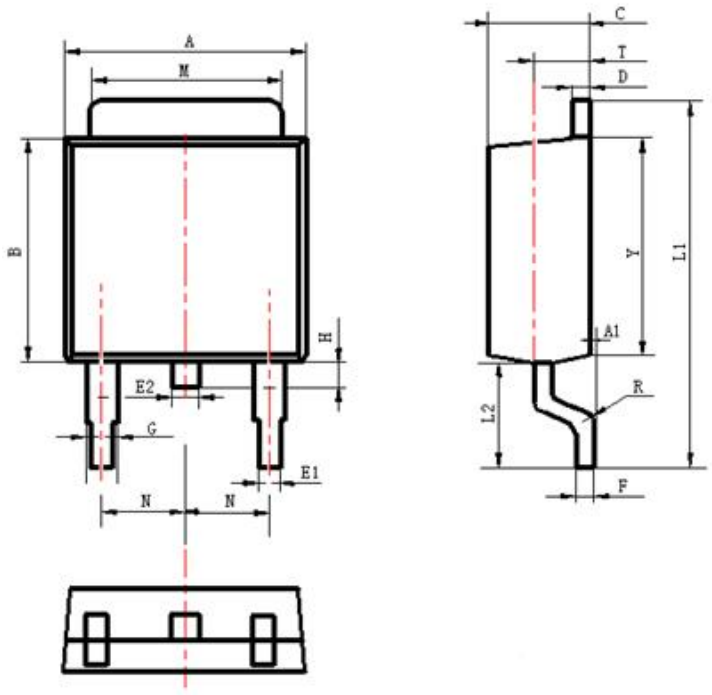
Figure 23. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Figure 24. Unclamped Inductive Switching Waveforms

Package Information：



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
A1	0	0.13
B	5.70	6.30
C	2.10	2.50
D	0.30	0.70
E1	0.60	0.90
E2	0.70	1.00
F	0.30	0.60
G	0.70	1.20
L1	9.60	10.50
L2	2.70	3.10
H	0.60	1.00
M	5.10	5.50
N	2.09	2.49
R	0.3	
T	1.40	1.60
Y	5.10	6.30

TO-252 Package

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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Revison History		
Revision	Date	Major changes
1.0	2026/4/13	Update logo